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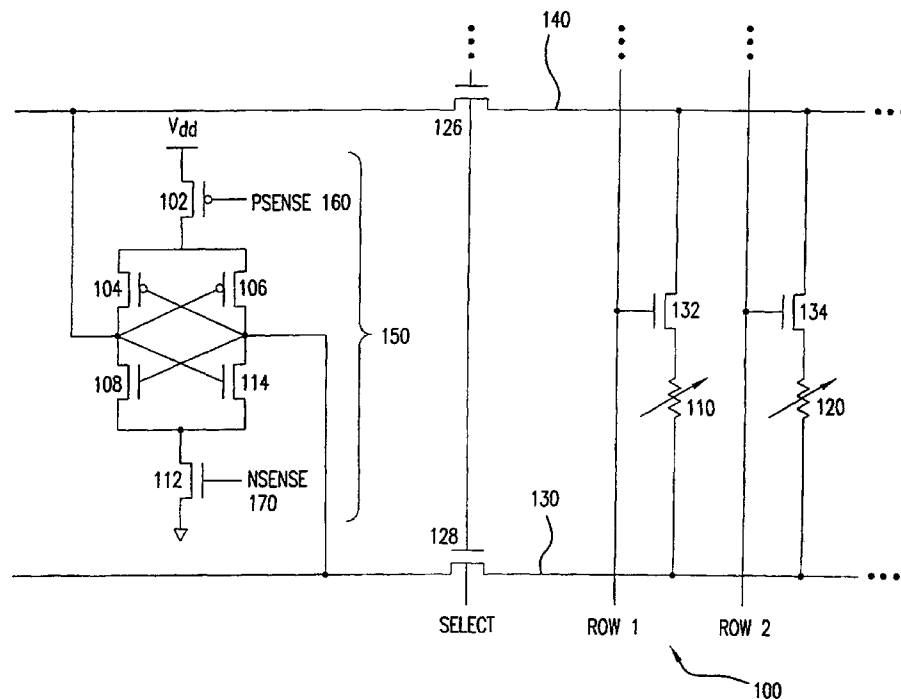
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(54) Title: SKEWED SENSE AMP FOR VARIABLE RESISTANCE MEMORY SENSING



(57) Abstract: A variable resistance memory sense amplifier has a built-in offset to assist in switching the sense amplifier when a resistive memory cell is in a low resistance state. The built-in offset can be achieved by varying size, threshold voltage, associated capacity or associated resistance of the transistors within the sense amplifier.

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